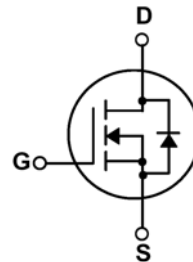
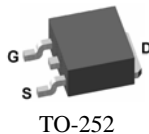


N-Channel Enhancement Mode MOSFET

Feature

- 30V/12A, $R_{DS(ON)} = 85\text{m}\Omega$ (MAX) @ $V_{GS} = 10\text{V}$.
 $R_{DS(ON)} = 100\text{m}\Omega$ (MAX) @ $V_{GS} = 4.5\text{V}$.
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- TO-252 for Surface Mount Package.



Applications

- Power Management in Desktop Computer or DC/DC Converters .

Absolute Maximum Ratings

 $T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	12	A

Electrical Characteristics

 $T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=24\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	1	-	2	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=12\text{A}$	-	60	85	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=6.0\text{A}$	-	65	100	$\text{m}\Omega$
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0\text{V}, I_S=6.0\text{A}$			2.1	V

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